

400W SURFACE-MOUNT TRANSIENT VOLTAGE SUPPRESSOR

Product Summary (@TA = +25°C)

VBR (MIN)	IPP (MAX)	Vc (MAX)
4.5V to 224V	1.2A to 43.8A	8.0V to 328V

Description and Applications

This new generation TVS is designed for transient overvoltage protection. The combination of small size and high ESD surge capability makes it ideal for use in:

- Power management
- Automotive
- · Battery contacts

Features

- 400W Peak Pulse Power Dissipation (10µs x 1000µs Waveform)
- 5V to 200V Standoff Voltages
- Provides ESD Protection per IEC61000-4-2 Standard: Air ±30kV, Contact ±30kV
- Excellent Clamping Capability
- Fast Response Time: Typically Less Than 1.0ns for Uni-Direction, Less Than 5.0ns for Bi-Direction, Form 0 Volts to BV Min.
- Lead-Free Finish; RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- The SMF4L3.3AQ SMF4L200(C)AQ are suitable for automotive applications requiring specific change control; these parts are AEC-Q101 qualified, PPAP capable, and manufactured in IATF 16949 certified facilities.

https://www.diodes.com/quality/product-definitions/

Mechanical Data

- Package: DO-219AA
- Package Material: Molded Plastic, "Green" Molding Compound.
 UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Matte Tin Finish Annealed over Copper Alloy Leadframe. Solderable per MIL-STD-202, Method 208 (3)
- Weight: 0.016 grams (Approximate)
- Polarity: Cathode Band Denotes Uni-Directional Device; None Cathode Band Denotes Bi-Directional Device

DO-219AA







Top View Bi-Directional Uni-Directional

Ordering Information (Note 4)

Orderable Part Number	Package	Reel Size (inches)	Tape Width (mm)	Pa	cking
Orderable Fait Number	Fackage	Reel Size (iliches)	rape widii (iiiii)	Qty.	Carrier
SMF4Lx.x(C)AQ-7	DO-219AA	7	12	3000	Tape & Reel
SMF4Lxx(C)AQ-7	DO-219AA	7	12	3000	Tape & Reel
SMF4Lxxx(C)AQ-7	DO-219AA	7	12	3000	Tape & Reel

- 1. EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant. All applicable RoHS exemptions applied.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.



Marking Information





ZZ = Product Type Marking Code (See Electrical Characteristics Table) YWXX = Date Code Marking Y = Year (ex: 5 = 2025) W = Week Code

XX = Journal Lot Code (ex: 0~9 and A~Z, (Skip O, I)) Bar Denotes Cathode Side

Date Code Key

Year	2021	-	2025	2026	2027	2028	2029	2030	2031	2032	2033	2034
Code	1	-	5	6	7	8	9	0	1	2	3	4
Week	Veek 1-26									27-52		
Code	Code A-Z							•	•	a-z	•	

Maximum Ratings (@TA = +25°C, unless otherwise specified.)

Single phase, half wave, 60Hz, resistive or inductive load. For capacitive load, derate current by 20%.

Characteristic	Symbol	Value	Unit
Peak Pulse Power Dissipation (Note 5) 10/1000µs	P _{PK}	400	W
Peak Forward Surge Current, 8.3ms Single Half Sine Wave (Note 6)	IFSM	40	Α
Maximum Instantaneous Forward Voltage at 16A for Uni-directional Device Only (Note 7)	VF	3	V

Thermal Characteristics

Characteristic	Symbol	Value	Unit
DC Steady-State Power Dissipation (Note 8)	PD	1.0	W
Typical Thermal Resistance (Note 9)	Reja Rejl Rejc	96 14 18	°C/W
Thermal Resistance, Junction to Soldering Point (Note 10)	R _{OJS}	70	°C/W
Operating and Storage Temperature Range	TJ, TSTG	-55 to +175	°C

- 5. Non-repetitive current pulse, per figure 4 and derated above T_A = +25°C, per figure 1.
- 6. 1/2 sine wave (or equivalent square wave), pulse width = 8.3ms, duty cycle = 4 pulses/minute maximum.
- 7. V_F max = 3V at I_F = 16A 300 μ s square wave pulse.
- 8. Device mounted on 1" \times 1", FR-4 PCB; 2 oz. Cu pad layout.
- 9. Thermal resistance from junction to ambient, lead and case.
- 10. Theoretical R_{0JS} calculated from the top center of the die straight down to the PCB/cathode tab solder junction.



Electrical Characteristics (TA = +25°C, unless otherwise specified.)

Туре	Number	Working Peak Reverse Voltage		kdown Vo Volts (No	_	Maximum Reverse Voltage at IRSM (Clamping Voltage)	Maximum Reverse Surge Current	Maximum Reverse Leakage at V _{RWM} (Note 12)	-	vice ig Code
Uni	Bi	V _{RWM} (Volts)	Min	Max	@I _T (mA)	V _{RSM} (Volts)	I _{RSM} (Amps)	I _R (μA)	Uni	Bi
SMF4L3.3AQ	_	3.3	4.5	6.0	10	8	43.8	100	HD	_
SMF4L5.0AQ	SMF4L5.0CAQ	5	6.4	7.07	10	9.2	43.5	800	HE	TE
SMF4L6.0AQ	SMF4L6.0CAQ	6	6.67	7.37	10	10.3	38.3	800	HG	TG
SMF4L6.5AQ	SMF4L6.5CAQ	6.5	7.22	7.98	10	11.2	35.7	500	HK	TK
SMF4L7.0AQ	SMF4L7.0CAQ	7	7.78	8.6	10	12	33.3	200	НМ	TM
SMF4L7.5AQ	SMF4L7.5CAQ	7.5	8.3	9.21	1	12.9	31	100	HP	TP
SMF4L8.0AQ	SMF4L8.0CAQ	8	8.89	9.83	1	13.6	29.4	50	HR	TR
SMF4L8.5AQ	SMF4L8.5CAQ	8.5	9.44	10.43	1	14.4	27.7	10	HT	TT
SMF4L9.0AQ	SMF4L9.0CAQ	9	10	11.1	1	15.4	26	5	HV	TV
SMF4L10AQ	SMF4L10CAQ	10	11.1	12.3	1	17	23.5	5	HX	TX
SMF4L11AQ	SMF4L11CAQ	11	12.2	13.5	1	18.2	22	0.5	HZ	TZ
SMF4L12AQ	SMF4L12CAQ	12	13.3	14.7	1	19.9	20.1	0.5	IE	UE
SMF4L13AQ	SMF4L13CAQ	13	14.4	15.9	1	21.5	18.6	0.5	IG	UG
SMF4L14AQ	SMF4L14CAQ	14	15.6	17.2	1	23.2	17.2	0.5	IK	UK
SMF4L15AQ	SMF4L15CAQ	15	16.7	18.5	1	24.4	16.4	0.5	IM	UM
SMF4L16AQ	SMF4L16CAQ	16	17.8	19.7	1	26	15.3	0.5	IP	UP
SMF4L17AQ	SMF4L17CAQ	17	18.9	20.9	1	27.6	14.5	0.5	IR	UR
SMF4L18AQ	SMF4L18CAQ	18	20	22.1	1	29.2	13.7	0.5	IT	UT
SMF4L20AQ	SMF4L20CAQ	20	22.2	24.5	1	32.4	12.3	0.5	IV	UV
SMF4L22AQ	SMF4L22CAQ	22	24.4	27	1	35.5	11.2	0.5	IX	UX
SMF4L24AQ	SMF4L24CAQ	24	26.7	29.5	1	38.9	10.3	0.5	ΙZ	UZ
SMF4L26AQ	SMF4L26CAQ	26	28.9	31.9	1	42.1	9.5	0.5	JE	VE
SMF4L28AQ	SMF4L28CAQ	28	31.1	34.4	1	45.4	8.8	0.5	JG	VG
SMF4L30AQ	SMF4L30CAQ	30	33.3	36.8	1	48.4	8.3	0.5	JK	VK
SMF4L33AQ	SMF4L33CAQ	33	36.7	40.6	1	53.3	7.5	0.5	JM	VM

^{11.} V_{BR} measured at pulse test current I_T with $t_P \le 5.0$ ms at T_A = +25°C. 12. The I_R limit is double for Bi-directional devices.

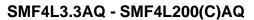


Electrical Characteristics (@TA = +25°C, unless otherwise specified.) (continued)

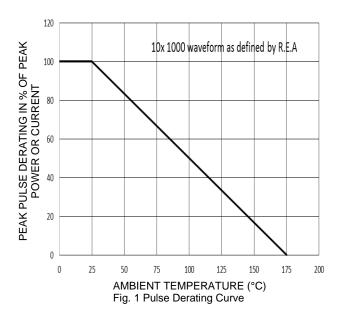
Туре	Number	Working Peak Reverse Voltage		Breakdown Voltage V _{BR} Volts (Note 11)		Maximum Reverse Voltage at Irsm (Clamping Voltage)	Maximum Reverse Surge Current	Maximum Reverse Leakage at V _{RWM} (Note 12)	Devi Marking	
Uni	Bi	V _{RWM} (Volts)	Min	Max	@I _T (mA)	V _{RSM} (Volts)	I _{RSM} (Amps)	I _R (μA)	Uni	Bi
SMF4L36AQ	SMF4L36CAQ	36	40	44.2	1	58.1	6.9	0.5	JP	VP
SMF4L40AQ	SMF4L40CAQ	40	44.4	49.1	1	64.5	6.2	0.5	JR	VR
SMF4L43AQ	SMF4L43CAQ	43	47.8	52.8	1	69.4	5.7	0.5	JT	VT
SMF4L45AQ	SMF4L45CAQ	45	50	55.3	1	72.7	5.5	0.5	JV	VV
SMF4L48AQ	SMF4L48CAQ	48	53.3	58.9	1	77.4	5.2	0.5	JX	VX
SMF4L51AQ	SMF4L51CAQ	51	56.7	62.7	1	82.4	4.9	0.5	JZ	VZ
SMF4L54AQ	SMF4L54CAQ	54	60	66.3	1	87.1	4.6	0.5	RE	WE
SMF4L58AQ	SMF4L58CAQ	58	64.4	71.2	1	93.6	4.3	0.5	RG	WG
SMF4L60AQ	SMF4L60CAQ	60	66.7	73.7	1	96.8	4.1	0.5	PK	WK
SMF4L64AQ	SMF4L64CAQ	64	71.1	78.6	1	103	3.9	0.5	RM	WM
SMF4L70AQ	SMF4L70CAQ	70	77.8	86	1	113	3.5	0.5	RP	WP
SMF4L75AQ	SMF4L75CAQ	75	83.3	92.1	1	121	3.3	0.5	RR	WR
SMF4L78AQ	SMF4L78CAQ	78	86.7	95.8	1	126	3.2	0.5	RT	WT
SMF4L85AQ	SMF4L85CAQ	85	94.4	104	1	137	2.9	0.5	RV	WV
SMF4L90AQ	SMF4L90CAQ	90	100	111	1	146	2.7	0.5	RX	WX
SMF4L100AQ	SMF4L100CAQ	100	111	123	1	162	2.5	0.5	RZ	WZ
SMF4L110AQ	SMF4L110CAQ	110	122	135	1	177	2.3	0.5	SE	XE
SMF4L120AQ	SMF4L120CAQ	120	133	147	1	193	2.0	0.5	SG	XG
SMF4L130AQ	SMF4L130CAQ	130	144	159	1	209	1.9	0.5	SK	XK
SMF4L150AQ	SMF4L150CAQ	150	167	185	1	243	1.6	0.5	SM	XM
SMF4L160AQ	SMF4L160CAQ	160	178	197	1	259	1.5	0.5	SP	XP
SMF4L170AQ	SMF4L170CAQ	170	189	209	1	275	1.4	0.5	SR	XR
SMF4L188AQ	SMF4L188CAQ	188	209	231	1	328	1.2	0.5	SS	VS
SMF4L200AQ	SMF4L200CAQ	200	224	248	1	324	1.2	0.5	ST	YT

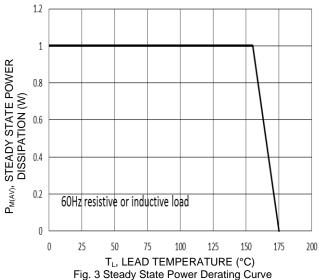
^{11.} V_{BR} measured at pulse test current I_T with $t_P \le 5.0 ms$ at $T_A = +25 ^{\circ}C$.

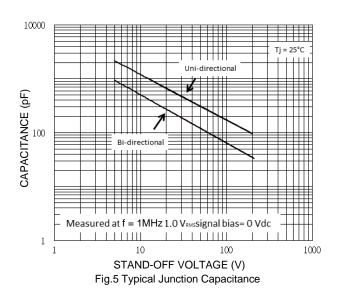
^{12.} The I_R limit is double for Bi-directional devices.

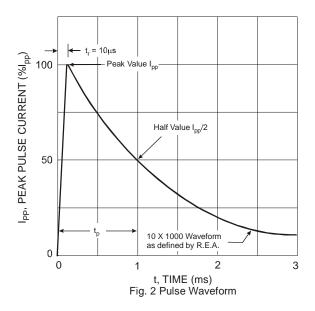


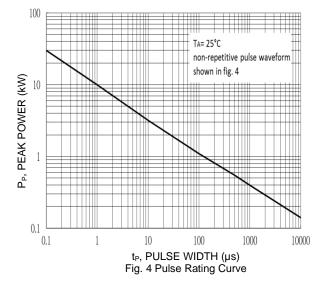










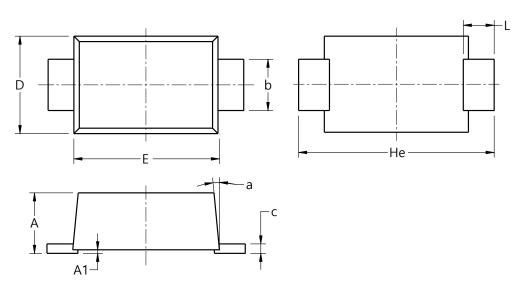




Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

DO-219AA

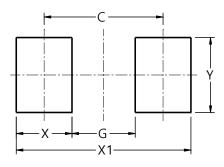


	DO-219AA									
Dim	Min	Max	Тур							
Α	0.81	1.20	1.18							
A1	0.03	0.10	0.07							
b	0.85	1.15	1.00							
С	0.05	0.30	0.15							
D	1.70	2.00	1.90							
Е	2.70	2.90	2.80							
He	3.50	3.90	3.80							
L	0.45	0.75	0.60							
а	0°	8°	5°							
All E	All Dimensions in mm									

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

DO-219AA



Dimensions	Value (in mm)
C	2.86
G	1.52
Х	1.34
X1	4.20
Υ	1.80



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